



# ST2408HI

## HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

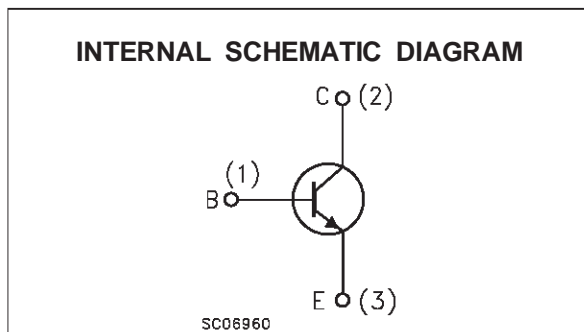
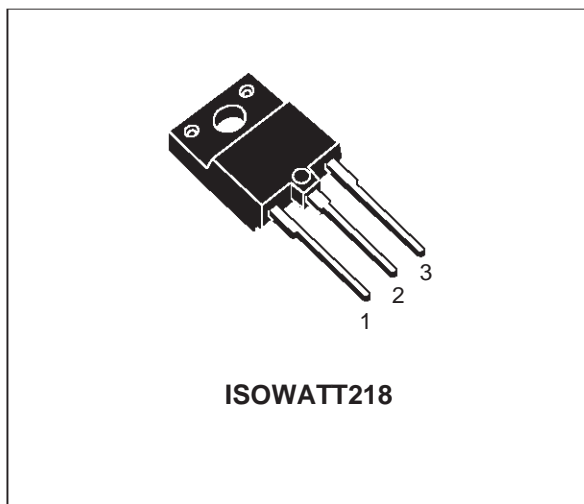
- NEW SERIES, ENHANCED PERFORMANCE
- FULLY INSULATED PACKAGE FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGHTER  $h_{fe}$  CONTROL
- IMPROVED RUGGEDNESS

### APPLICATIONS:

- HORIZONTAL DEFLECTION FOR MONITOR 17" AND HIGH END TV

### DESCRIPTION

The device is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	1500	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	600	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	7	V
$I_C$	Collector Current	12	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	25	A
$I_B$	Base Current	7	A
$P_{tot}$	Total Dissipation at $T_C = 25$ °C	55	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

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## THERMAL DATA

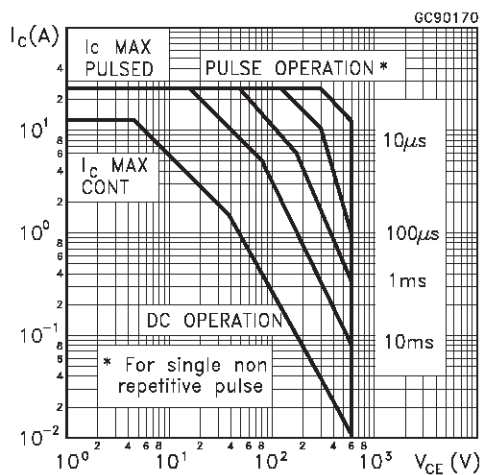
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	2.3	°C/W
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## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

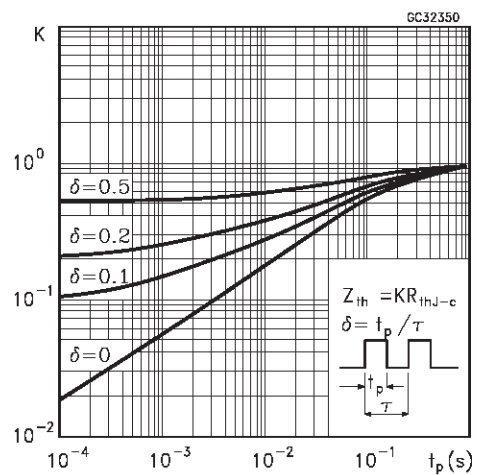
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1500 V			1	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 7 V			1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA L = 25 mH	600			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8 A I <sub>B</sub> = 2 A			3	V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8 A I <sub>B</sub> = 2 A			1.5	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 1 A V <sub>CE</sub> = 5 V I <sub>C</sub> = 8 A V <sub>CE</sub> = 5 V	6	25	9	
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 7 A f <sub>h</sub> = 82 KHZ I <sub>B(on)</sub> = 1.5 A V <sub>BB(off)</sub> = -2.5 V L <sub>B</sub> = 0.4 μH		2.1 110	2.4 150	μs ns

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

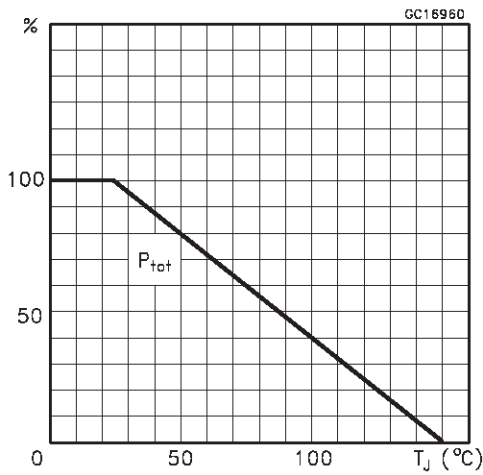
## Safe Operating Area



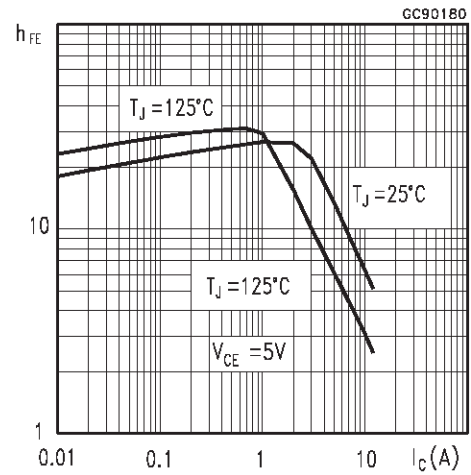
## Thermal Impedance



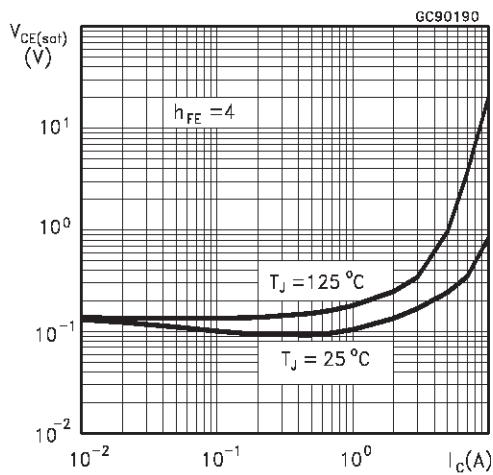
Derating Curve



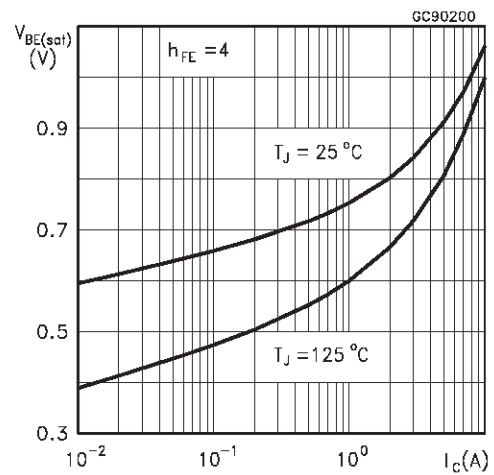
DC Current Gain



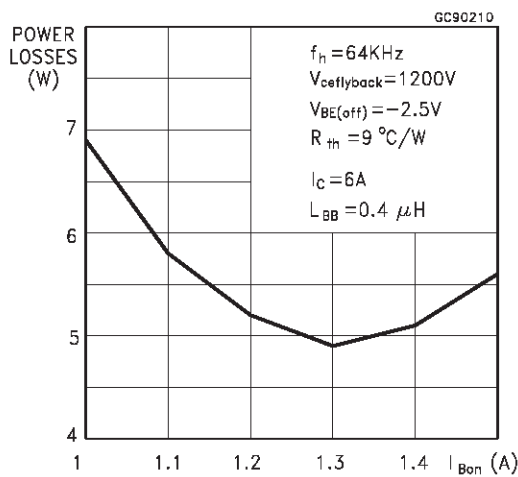
Collector Emitter Saturation Voltage



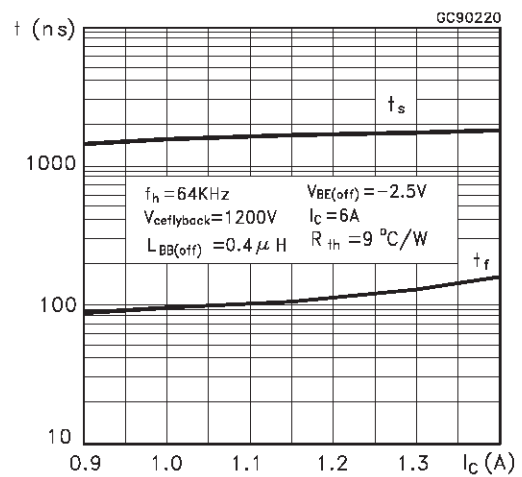
Base Emitter Saturation Voltage



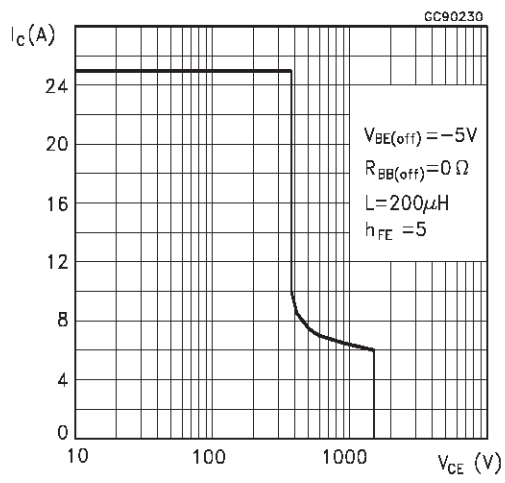
Power Losses



Switching Time Inductive Load



Reverse Biased Soa





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